

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **BLV80-28** is Designed for 28 Volt Class C VHF Power Amplifier Applications up to 175 MHz.

**FEATURES:**

- $\eta_C = 65\%$  min. at 80 W/175 MHz
- $P_G = 6.5$  dB min. at 80 W/175 MHz
- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

$I_C$	9.0 A
$V_{CBO}$	65 V
$V_{CEO}$	35 V
$P_{DISS}$	117 W @ $T_C = 25^\circ C$
$T_J$	$-65^\circ C$ to $+200^\circ C$
$T_{STG}$	$-65^\circ C$ to $+150^\circ C$
$\theta_{JC}$	$1.5^\circ C/W$

**PACKAGE STYLE .500 4L FLG**

	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	220/5,59	230/5,84
B	.125/3,18	
C	245/6,22	255/6,48
D	720/18,28	730/18,54
E	.125/3,18	
F	970/24,64	980/24,89
G	495/12,57	505/12,83
H	003/0,08	007/0,18
I	090/2,29	110/2,79
J	160/4,06	175/4,45
K	280/7,11	
L	1050/26,67	

**ORDER CODE: ASI10797**

**CHARACTERISTICS**  $T_C = 25^\circ C$ 

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CBO}$	$I_C = 20$ mA	65			V
$BV_{CEO}$	$I_C = 200$ mA	35			V
$BV_{EBO}$	$I_E = 10$ mA	4.0			V
$I_{CBO}$	$V_{CB} = 30$ V			1.5	mA
$h_{FE}$	$V_{CE} = 25$ V $I_C = 3.5$ A	15		100	---
$C_{OB}$	$V_{CB} = 30$ V $f = 1.0$ MHz			150	pF
$P_G$	$V_{CC} = 25$ V $P_{OUT} = 80$ W $f = 175$ MHz	6.5	7.0		dB
$\eta_C$		65			%